



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

## Digital transistors (built-in resistors)

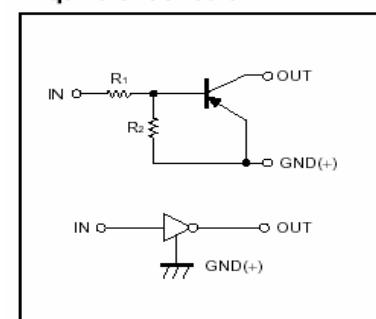
### DTA123YE/ DTA123YUA/ DTA123YCA/DTA123YKA/DTA123YSA

DIGITAL TRANSISTOR (PNP)

#### Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.

#### ●Equivalent circuit



#### PIN CONNECTIONS AND MARKING

DTA123YE SOT-523 Addreviated symbol: 52	 1.IN 2.GND 3.OUT	DTA123YUA SOT-323 Addreviated symbol: 52	 1.IN 2.GND 3.OUT
DTA123YKA SOT-23-3L Addreviated symbol: 52	 1.IN 2.GND 3.OUT	DTA123YCA SOT-23 Addreviated symbol: 52	 1.IN 2.GND 3.OUT
DTA123YSA TO-92S	 1.GND 2.OUT 3.IN (1) (2) (3)		

## Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits (DTA123Y□ )					Unit		
		E	UA	KA	CA	SA			
Supply voltage	V <sub>CC</sub>	-50					V		
Input voltage	V <sub>IN</sub>	-12~5					V		
Output current	I <sub>O</sub>	-100					mA		
	I <sub>C(MAX)</sub>	-100							
Power dissipation	P <sub>d</sub>	150		200		300	mW		
Junction temperature	T <sub>j</sub>	150					°C		
Storage temperature	T <sub>stg</sub>	-55~150					°C		

## Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	V <sub>I(off)</sub>			-0.3	V	V <sub>CC</sub> =-5V ,I <sub>O</sub> =-100μA
	V <sub>I(on)</sub>	-3				V <sub>O</sub> =-0.3V ,I <sub>O</sub> =-20 mA
Output voltage	V <sub>O(on)</sub>			-0.3	V	I <sub>O</sub> /I <sub>I</sub> =-10mA/-0.5mA
Input current	I <sub>I</sub>			-3.8	mA	V <sub>I</sub> =-5V
Output current	I <sub>O(off)</sub>			-0.5	μA	V <sub>CC</sub> =-50V ,V <sub>I</sub> =0
DC current gain	G <sub>I</sub>	33				V <sub>O</sub> =-5V ,I <sub>O</sub> =-10mA
Input resistance	R <sub>I</sub>	1.54	2.2	2.86	KΩ	
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	3.6	4.5	5.5		
Transition frequency	f <sub>T</sub>		250		MHz	V <sub>O</sub> =-10V ,I <sub>O</sub> =5mA,f=100MHz

## Typical Characteristics

### ●Electrical characteristic curves

